Origin and stabilization of ferrielectricity in CuInP$_2$Se$_6$

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Using first-principles calculations and group-theoretical methods, we study the origin and stabilization of ferrielectricity (FiE) in CuInP$_2$Se$_6$. We find that the polar distortions of the metal atoms create most of the polarization in the FiE phase. Surprisingly, the stabilization of the FiE phase comes from an anharmonic coupling between the polar mode and a fully symmetric Raman-active mode comprising primarily of the Se atoms. This coupling is large even down to the monolayer limit, and the degree of anharmonicity is comparable to improper ferroelectrics. Our results open up possibilities for dynamical control of the single-step ferroelectric switching barrier by tuning the Raman-active mode. These findings have important implications not only for designing next-generation microelectronic devices that can overcome the voltage-time dilemma but also in explaining the unconventional devices observed in CuInP$_2$Se$_6$ and similar layered thiophosphates.

TABLE I. The computed structural parameters for the paraelectric (PE) phase of CIPSe with space group $P\overline{3}1c$ are compared to the corresponding experimental values [25]. $a$ and $c$ are the lattice constants. The Wyckoff positions of the symmetry inequivalent atoms are also listed with the corresponding experimental values shown in brackets.

<table>
<thead>
<tr>
<th>Atom</th>
<th>Wyckoff site</th>
<th>$x$</th>
<th>$y$</th>
<th>$z$</th>
<th>Exp.</th>
</tr>
</thead>
<tbody>
<tr>
<td>Cu</td>
<td>2d</td>
<td>0.667 (0.667)</td>
<td>0.333 (0.333)</td>
<td>0.25 (0.25)</td>
<td></td>
</tr>
<tr>
<td>In</td>
<td>2a</td>
<td>0 (0)</td>
<td>0 (0)</td>
<td>0.25 (0.25)</td>
<td></td>
</tr>
<tr>
<td>P</td>
<td>4f</td>
<td>0.333 (0.333)</td>
<td>0.667 (0.667)</td>
<td>0.164 (0.166)</td>
<td></td>
</tr>
<tr>
<td>Se</td>
<td>12i</td>
<td>0.349 (0.331)</td>
<td>0.340 (0.340)</td>
<td>0.120 (0.120)</td>
<td></td>
</tr>
</tbody>
</table>

I. INTRODUCTION

When designing memory-elements one typically has to choose between either a low-voltage of operation or a faster switching speed due to their contrasting dependence on the switching barrier. This compromise is referred to as the voltage-time dilemma [1]. Identifying materials where the origin of the order parameter that defines the memory state is different from the factors that stabilizes it has the potential to overcome this inherent bottleneck. Much materials offer a path for independent control of the switching barrier and the order parameter.

Recently, ferroelectricity in layered van der Waal’s materials has attracted a lot of attention because of its applications in high-density nonvolatile memory devices [2–4]. However, very few layered materials demonstrate switchable out-of-plane polarization [5–10]. Of those, the transition metal thiophosphates are a promising family of materials that host out-of-plane ferrielectricity (FiE) with large values of polarization [6, 11, 12]. Further, research efforts in these materials have reported a plethora of properties including negative piezoelectricity, negative electrostriction, large dielectric tunability, and unconventional field-induced switching behavior, all of which depend strongly on the polarization [13–23]. Despite the growing interest, a clear understanding of the origin and stabilization of the polar phase is still lacking in transition metal thiophosphate.

In this article, using density functional theory (DFT) calculations and group-theoretical methods we discuss the origin and structural stabilization of polarization in transition metal thiophosphates using CuInP$_2$Se$_6$ (CIPSe) as an example. We find that the polar displacements of the Cu and In atoms create most of the polarization in the FiE phase. Surprisingly, this polar distortion alone does not lead to a gain in the energy, and even the full polar mode leads to a very shallow double-well potential (2 meV/Cu). We report that a strong anharmonic coupling between the polar mode and a fully symmetric Raman-active mode is necessary to stabilize the polar phase. While such a coupling is symmetry allowed even in conventional ferroelectrics, we find that its magnitude is surprisingly large in CIPSe. In fact, it is an order of magnitude larger (-356.7 meV) than the corresponding harmonic coupling coefficient (-47.1 meV), and the degree of anharmonicity is comparable to known improper ferroelectrics such as YMnO$_3$ [24]. This large non-linear coupling between the polar mode and the fully symmetric Raman-active mode is expected to play an important role in determining the switching dynamics of the polarization. By analysing the various contributions to the total energy we discuss the microscopic origin of this large coupling. Finally, we demonstrate that strain can be an effective knob to both enhance and suppress the FiE phase.

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FIG. 1. The crystal structure and the atomic distortions in the paraelectric (PE) and ferrielectric (FiE) phases of CuInP$_2$Se$_6$ (CIPSe). (a) The top-view and (b) the side-view of the PE phase ($P31c$) with one of the inversion center labeled ('×'). (c) The top-view and (d) the side-view of the FiE phase ($P31c$). The FiE phase can be decomposed into six symmetry adapted polar modes and four symmetry adapted fully symmetric modes that transform as the $\Gamma_2^−$ and $\Gamma_1^+$ irreducible representation (irrep) of $P31c$, respectively. The arrows represent the local distortions. All the arrows have the same amplitude. (e) The displacement of the Cu atom towards the top trigonal Se$_t$-plane ($\Gamma_2^−[A_3]$). (f) The expansion (contraction) of the trigonal Se$_t$ (Se$_b$) planes ($\Gamma_2^−[A_3]$), and (g) the in-phase rotation of the Se$_t$ and Se$_b$-planes about the Cu atoms ($\Gamma_2^−[A_2]$). (h) The out-of-plane expansion of the Se sub-layers ($\Gamma_1^+[A_3]$), and (i) the in-phase rotation of the Se$_t$ and Se$_b$-planes about the Cu atoms.

TABLE II. The computed structural parameters for the FiE phase of CIPSe with space group $P31c$ are compared to the corresponding experimental values [19]. $a$ and $c$ are the lattice constants. The Wyckoff positions of the symmetry inequivalent atoms are also listed with the corresponding experimental values shown in brackets.

<table>
<thead>
<tr>
<th>Atom</th>
<th>Wyckoff site</th>
<th>$x$</th>
<th>$y$</th>
<th>$z$</th>
</tr>
</thead>
<tbody>
<tr>
<td>Cu</td>
<td>2b</td>
<td>0.667 (0.667)</td>
<td>0.333 (0.333)</td>
<td>0.167 (0.147)</td>
</tr>
<tr>
<td>In</td>
<td>2a</td>
<td>0 (0)</td>
<td>0</td>
<td>0.268 (0.259)</td>
</tr>
<tr>
<td>P$_t$</td>
<td>2b</td>
<td>0.333 (0.333)</td>
<td>0.667 (0.667)</td>
<td>0.340 (0.326)</td>
</tr>
<tr>
<td>P$_b$</td>
<td>2b</td>
<td>0.333 (0.333)</td>
<td>0.667 (0.667)</td>
<td>0.170 (0.158)</td>
</tr>
<tr>
<td>Se$_t$</td>
<td>6c</td>
<td>0.310 (0.301)</td>
<td>0.325 (0.323)</td>
<td>0.118 (0.110)</td>
</tr>
<tr>
<td>Se$_b$</td>
<td>6c</td>
<td>0.358 (0.355)</td>
<td>0.008 (0.005)</td>
<td>0.384 (0.371)</td>
</tr>
</tbody>
</table>

$\text{a}$  The additional three out-of-plane polar modes ($\Gamma_2^−[A_3]$) involving only one of the In, P or Se atoms are not shown for the sake of clarity.

$\text{b}$  The out-of-plane breathing modes involving only the P atoms ($\Gamma_1^+[A_3]$; P) is not shown for the sake of clarity.

II. CRYSTAL STRUCTURE

We chose the bulk ordered high-symmetry structure of CIPSe with space group $P31c$ (see Fig. 1 (a)-(b)) as the reference paraelectric (PE) structure for studying the FiE phase [27]. Details of the calculation including the DFT methodology are described in Ref. [28]. The computed lattice parameters and the occupied Wyckoff positions agree well with the average experimental parameters in the $P31c$ phase (see Table I) [25]. The crystal structure is similar to the transition metal trichalcogenides with a trigonal lattice [29, 30]. However, two different atoms (Cu and In) occupy the metal site. This naturally creates an inversion-asymmetry within each layer. The Cu and In ions have a nominal charge of +1 and +3, respectively, resulting in an outer-shell electronic configuration of d$^{10}$ for both the atoms. They both are octahedrally coordinated by six Se atoms. The layers are stacked such that the P$_2$Se$_6$ ligand sits on top of the Cu atom from the other layer, thereby, recovering inversion symmetry. This interlayer inversion center is labeled (‘×’) in Fig. 1.
A. Structural distortions in the FiE phase

The relaxed crystal structure of the FiE phase with space group P31c is shown in Fig.(c)-(d). The computed lattice parameters and Wyckoff positions compare well with the corresponding experimental values (see Table II) [19]. The Cu and In atoms exhibit an anti-parallel out-of-plane distortion relative to each other. Further, the P and Se Wyckoff sites are split into two sites each, corresponding to the top and bottom sub-layers within each monolayer. We label the top (bottom) trigonal Se-plane within each CIPSe layer as Se$_t$ (Se$_b$).

The polar mode that transforms as the $\Gamma_2$—irreducible representation (irrep) of $P31c$ is the primary order parameter for the transition from the PE phase to the FiE phase. There are six symmetry-adapted modes that transform as the $\Gamma_2$—irrep. Four of them are labeled $\Gamma_2 - [A_3]$, and involve the displacement of the four atom types along the out-of-plane direction of one. Fig. 1 (e) shows the $\Gamma_2 - [A_3]$ mode for the Cu atom. In addition, there are two symmetry adapted modes comprising of the in-plane distortions of the Se octahedron. The first mode labeled $\Gamma_2 - [A_1]$ is a breathing mode corresponding to the expansion (compression) of the trigonal Se$_b$-(Se$_t$-)plane along (away from) the direction of the Cu displacement (see Fig. 1 (f)). This results in an in-phase rotation of the trigonal Se-planes about the P$_2$ bond. The second mode labeled $\Gamma_2 - [A_2]$ is a breathing mode about the P$_2$ bond (see Fig. 1 (g)), resulting in an in-phase rotation about the Cu atoms. The polar mode is made up of a combination of these six symmetry adapted modes.

In addition, the polar mode induces a Raman-active mode which preserves the full symmetry of the parent space group (labeled $\Gamma_1$+). This mode in turn is made up of a combination of four symmetry adapted modes that involve the displacement of only the P and Se atoms. Two of these symmetry adapted modes are labeled $\Gamma_1 + [A_3]$ and correspond to the out-of-plane expansion of the individual P and Se layers. Fig. 1 (h) shows this $\Gamma_1 + [A_3]$ mode for the Se atoms. The other two modes involve the in-plane distortion of the trigonal Se-planes, and are labeled $\Gamma_1 + [A_1]$ and $\Gamma_1 + [A_2]$. The $\Gamma_1 + [A_1]$ mode corresponds to the expansion of both the top and bottom trigonal Se-planes about the Cu atoms (see Fig. 1 (i)), whereas the $\Gamma_1 + [A_2]$ mode involve the out-of-phase rotation of the top and bottom trigonal Se-planes about the Cu atoms (see Fig. 1 (j)).

B. The origin of polarization

Table III shows the amplitude of the corresponding symmetry adapted modes in the FiE phase [31]. Notably, the largest distortion involves the out-of-plane motion of the Cu atoms towards the Se$_t$ trigonal face (labeled $\Gamma_2 - [A_3]$: Cu), and has an amplitude of 1.15 Å. Such a large distortion is atypical even for ferroelectrics. It is reasonable to assume that this will lead to large anharmonicity in the phonon modes, as we demonstrate in Sec. III.

We verified that the polarization is primarily originating from the polar modes (see Supplementary) [28]. Further, Table IV lists the atom-projected polarization with respect to the PE phase. The polar distortions of the Cu and In atoms carry a large polarization of 2.58 $\mu$C/cm$^2$, respectively. As the Born-effective charge for In (2.24) is larger than that of Cu (0.90), a relatively small displacement of In atoms (0.18 Å) can carry a large dipole moment. This results in the reported FiE phase with partial cancellation of polarization between the two sites, and a net polarization along the direction of the Cu displacement.

Table III shows the amplitude of the various symmetry adapted modes that transforms like the $\Gamma_1^3$ (fully symmetric mode) and the $\Gamma_2$ (polar mode) irreps of the PE phase (space group P31c) of CIPSe. Fig. 1 shows the corresponding symmetry adapted distortions.

<table>
<thead>
<tr>
<th>Symmetry adapted modes in P31c</th>
<th>Amplitude (Å)</th>
</tr>
</thead>
<tbody>
<tr>
<td>$\Gamma_1 + [A_3]$: P</td>
<td>-0.01</td>
</tr>
<tr>
<td>$\Gamma_1 + [A_3]$: Se</td>
<td>0.03</td>
</tr>
<tr>
<td>$\Gamma_1 + [A_1]$: Se</td>
<td>0.08</td>
</tr>
<tr>
<td>$\Gamma_1 + [A_2]$: Se</td>
<td>0.03</td>
</tr>
<tr>
<td>$\Gamma_2 - [A_3]$: Cu</td>
<td>1.15</td>
</tr>
<tr>
<td>$\Gamma_2 - [A_3]$: In</td>
<td>-0.18</td>
</tr>
<tr>
<td>$\Gamma_2 - [A_3]$: Se</td>
<td>0.05</td>
</tr>
<tr>
<td>$\Gamma_2 - [A_1]$: Se</td>
<td>0.13</td>
</tr>
<tr>
<td>$\Gamma_2 - [A_2]$: Se</td>
<td>0.00</td>
</tr>
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</table>

Table IV. The contribution to polarization from the distortions of the various atoms with respect to the PE phase.

<table>
<thead>
<tr>
<th>Atom</th>
<th>Polarization ($\mu$C/cm$^2$)</th>
</tr>
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<tbody>
<tr>
<td>Cu</td>
<td>6.17</td>
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<tr>
<td>In</td>
<td>-2.71</td>
</tr>
<tr>
<td>Se</td>
<td>-0.21</td>
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<tr>
<td>CuIn</td>
<td>3.29</td>
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<td>CuSe</td>
<td>5.60</td>
</tr>
<tr>
<td>InSe</td>
<td>-3.82</td>
</tr>
<tr>
<td>CuInSe (FiE-phase)</td>
<td>2.58</td>
</tr>
</tbody>
</table>

III. THE STRUCTURAL STABILIZATION OF THE FiE PHASE

While the Cu and In atoms lead to most of the polarization in the FiE phase, surprisingly, from Fig. 2 we find...
that neither the individual distortion of the Cu atoms (blue lines) nor In atoms (orange line), nor the collective ferroelectric distortion of both the atoms (red lines) creates a double-well potential with respect to the PE phase [33]. This is in sharp contrast to conventional oxide ferroelectrics where the dominant polar distortion on its own can lead to a double-well potential [34].

The energy profile for the full polar-instability in the PE phase (black curve in Fig. 2) shows a shallow double-well potential (2 meV). This highlights the importance of the collective distortion of all atoms that transform as the \( \Gamma_2^- \) irrep of \( P31c \) rather than just the displacement of Cu (or In) atom as discussed in prior research [12–14], as the primary order parameter for understanding the symmetry lowering phase transition in CIPSe. Interestingly, both the well-depth and amplitude of the polar mode at the minimum are much smaller than that of the fully-relaxed FiE phase. The fully-relaxed FiE phase has an energy gain of 98 meV/Cu with respect to the PE phase compared to an energy gain of 2 meV/Cu in the unrelaxed case. This large energy difference immediately suggests that the microscopic mechanism that stabilizes the polarization is different from the one that gives rise to it.

### A. Total energy surface

To explain the above mentioned discrepancy we compute the energy surface by varying fractional amplitudes of the fully symmetric mode (\( Q_{\Gamma_1^+,+} \)) and the polar mode (\( Q_{\Gamma_2^-} \))(see Fig. 3 (a)). These modes induce local distortions proportional to that listed in Table III. The lattice parameters are fixed to that of the fully relaxed PE phase. This free energy (\( F \)) can be written as,

\[
F = E_0 + b_{02}Q_{\Gamma_2^-} + b_{04}Q_{\Gamma_1^+}^4 + b_{06}Q_{\Gamma_2^-}^6 \\
+ b_{08}Q_{\Gamma_2^-}^8 + c_{12}Q_{\Gamma_1^+}^2 + c_{14}Q_{\Gamma_1^+}Q_{\Gamma_2^-} + c_{16}Q_{\Gamma_1^+}Q_{\Gamma_2^-}^2 + a_{20}Q_{\Gamma_1^+}^2,
\]

where \( E_0 \) is the energy of the PE phase that is set to zero, \( a_{ij} \) and \( b_{ij} \) are the real-valued coefficients of the expansion about \( Q_{\Gamma_1^+,+} \) and \( Q_{\Gamma_2^-} \), respectively. \( c_{ij}'s \) are the real-valued coefficients corresponding to the coupling between the two modes that are typically ignored in the case of oxides as they are considered to be small [24, 35]. They have also been completed ignored in prior works on CIPSe [12]. We will show that such an anharmonic coupling is crucial to the stabilization of the polar phase, and is key to controlling the polarization in CIPSe.

Table V shows the coefficients obtained from fitting the energy surface in Fig. 3 (a). We find \( b_{02} \) to be negative and \( b_{04} \) to be positive as expected of a characteristic double-well potential due to a polar-instability [36]. However, from Table V it is clear that the anharmonic coupling is anomalously large with \( c_{14} \) about 8 times larger than the harmonic term. This is comparable to the improper ferroelectric coupling between the polar mode and the zone-boundary mode in \( Y\mathrm{MnO}_3 \) [24]. The effective quadratic coefficient \( c^{eff}_{02} \) including the anharmonic terms from Eqn. 1 is,

\[
c^{eff}_{02} = (b_{02} + c_{12}Q_{\Gamma_1^+}).
\]

The strong anharmonic coupling renormalizes \( c^{eff}_{02} \) to become more negative. Similar renormalization of the optimal polarization and the Curie-Weiss temperature in conventional oxide ferroelectrics was discussed due to electrostriction [36]. But an anomalously large contribution of the fully symmetric mode leading to this renormalization as we find in CIPSe, is new and surprising.

<table>
<thead>
<tr>
<th>( b_{02} )</th>
<th>( b_{04} )</th>
<th>( b_{06} )</th>
<th>( b_{08} )</th>
<th>( c_{12} )</th>
<th>( c_{14} )</th>
<th>( a_{20} )</th>
</tr>
</thead>
<tbody>
<tr>
<td>-47.1</td>
<td>245.7</td>
<td>-116.0</td>
<td>17.3</td>
<td>-356.7</td>
<td>100.1</td>
<td>102.6</td>
</tr>
</tbody>
</table>
To elucidate the physical origin of the large nonlinear coupling between the polar mode and the fully symmetric mode, we analyzed the various contributions to the total energy. Figure 3 (b) and (c) shows the contributions from the Kohn-Sham eigenvalues and the Ewald energy - i.e., the electrostatic ion-ion interaction term, respectively, for the FiE phase relative to the PE phase. This is shown as a function of $Q_{Γ_1^+}$ and $Q_{Γ_2^-}$. We find that the polar mode lowers the total energy by reducing the Kohn-Sham electronic contribution to the energy (see Fig. 3 (b)). But the condensation of the polar mode results in a large Ewald energy penalty (see Fig. 3 (c)). The coupling between the polar mode and the fully symmetric mode overcomes this energy penalty.

As the Cu atoms move closer to the Se atoms thereby lowering the electronic-structure energy, the Ewald part of the total energy goes up due to an increased ion-ion repulsion. Such a competition between the electronic degrees of freedom and the repulsive forces between the ions is in line with a second-order Jahn-Teller effect [11, 36–39]. However, this shorter Cu-Se bond can be stabilized by an expansion (contraction) of the trigonal Se$_t$ (Se$_b$)-plane. The distortion of the trigonal Se-planes is dominated by the $A_1$ modes of both $Γ_{2^-}$ and $Γ_{1^+}$ (see Table III). As the expansion of the Se$_t$-plane does not have the same amplitude as the contraction of the Se$_b$-plane, a $Γ_{1^+}$ mode is additionally needed to stabilize the displaced Cu atoms naturally leading to a coupling between the modes. This is consistent with prior x-ray diffraction studies in this class of compounds [11]. So, the stabilization of the FiE phase in CIPSe is mediated by the chalcogen atoms that contributes to the fully symmetric Raman active mode.

Our analysis gives a clear microscopic mechanism of the unusual coupling between the polar mode and the fully symmetric mode that leads to the stabilization of the FiE phase. We find that this anharmonic stabilization persists even in the monolayer limit (see supplementary) [28]. Our results open up new routes for switching polarization in CIPSe, for e.g., by mechanically inducing a strain-field which transforms as the $Γ_{1^+}$ irrep of the PE space-group.

**IV. STRAIN-CONTROL OF FiE**

Previous works on oxides showed that polar-distortions naturally couple to strain [34, 40]. Here we discuss the case of an in-plane bi-axial strain ($\epsilon_{x^2+y^2}$), which uniformly expands (compress) the 2D-area for positive (negative) values. This component of the strain mode transforms as the $Γ_1^+$ irrep of the space group $P31c$. We expect this component of the strain to have a larger effect on the anharmonic coupling as this directly alters the area of the chalcogen sub-layers.

Figure 4 shows the total energy profile for the FiE polarization in CIPSe, for e.g., by mechanically inducing a strain-field which transforms as the $Γ_{1^+}$ irrep of the PE space-group.
phase relative to the PE phase for various value of $\epsilon_{x^2+y^2}$. For the unstrained case (red solid line) we recover the FiE phase as the low-energy state. We find that for a compressive strain of 1 % (green line) the FiE phase, although a local minimum, has higher energy (4 meV/Cu) than the PE phase. Such a small energy difference between the FiE phase and the PE phase separated by a small energy barrier (12 meV/Cu) could lead to the strain-stabilization of quantum paraelectricity where quantum fluctuations suppress the ordering of dipole moments [41, 42].

For a compressive strain of 2 % (magenta line) the polar instability is fully suppressed and the PE phase becomes the lowest energy structure. On the other hand, for a tensile strain (1 % shown in black lines and 2 % shown in blue line) the well-depth around the FiE phase becomes deeper. Thus, mechanical strain can be an effective tool to both suppress and enhance the FiE phase, providing a way to tune the energy barrier corresponding to a single-step switching of the polarization.

V. CONCLUSIONS AND OUTLOOK

Our analysis suggests that the barrier that needs to be overcome in a single-step switching of polarization from the up-state to the down-state is determined primarily by a large nonlinear coupling between the polar mode and the fully symmetric Raman-active mode. This understanding opens up possibilities to both enhance and suppress the energy barrier for polarization switching by modifying the fully symmetric mode, instead of the polar mode. Since the fully symmetric mode is Raman active, in addition to mechanical strain, it should also couple to ultra-fast optical probes allowing for the optical control of the switching barrier. [43–45].

In summary, we elucidate the origin and structural-stabilization of ferrielectricity in CIPSe. The distortions of the Cu and In atoms create most of the polarization in FiE CIPSe. On the other hand, the in-plane fully symmetric distortions of the Se atoms stabilizes the FiE phase via an anharmonic coupling to the polar mode. This coupling is an order of magnitude larger than the corresponding harmonic coupling coefficient. As the origin of the polarization is different from the factors that stabilizes it, the energy barrier for the single-step switching of the polarization in CIPSe can be controlled independently of the polarization itself. This can help overcome the voltage-time dilemma in microelectronic device applications. Our insights also have important implications in understanding the unconventional responses that depend on the polarization observed in transition metal thiophosphates. Further, CIPSe could potentially be driven into a quantum paraelectric phase by the application of a nominal strain.

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P.G. designed and oversaw the entire project. N.S. performed all calculations and analysis. N.S. also produced the first draft of the manuscript which was rewritten subsequently by all authors.

[27] A disorder phase with the space group P31c has also been proposed as the high-symmetry PE phase [13]. As the primary purpose of this letter is to understand the origin and the stabilization of local dipoles in CIPSe, we use the ordered high-symmetry phase as the parent structure.
[31] While reporting the distortion amplitudes the center of mass of the P$_2$ atoms is used as the origin. This choice does not affect our results.
[33] While one might conclude from Fig. 2 that the energy-surface for In displacement (orange) is flatter compared to the Cu displacement (blue), this is not the case. The energy reported is with respect to the fractional shift of the atoms. From Table III, we can see that the amplitude of the shift of the Cu atoms is more than six times that of the In atoms.
[37] S. Lee, P. Colombet, G. Ouvrard, and R. Brec, General trends observed in the substituted thiophosphate family, synthesis and structure of silver scandium thiophosphate, Ag$_2$ScP$_2$Se$_6$, and cadmium iron thiophosphate, CdFeP$_2$Se$_6$, Inorganic Chemistry, Inorganic Chemistry 27, 1291 (1988).
VI. SUPPLEMENTAL MATERIAL: ORIGIN AND STABILIZATION OF FERRIELECTRICITY IN CuInP₂Se₆

A. Methodology

We computed the first-principles total energies using Vienna ab initio simulation package (VASP) [46], with the PBE functional including van der Waals correction as implemented by Grimme (DFT-D2) [47]. Structural relaxation was done with a force convergence tolerance of 0.1 meV/Å using a conjugate-gradient algorithm. We found that the total force is less than 0.1 meV/Å. The convergence criterion for the electronic self-consistent calculations was set to 10⁻¹⁸ eV. A regular G-centered k-point grid was used to sample the Brillouin zone with a plane-wave cutoff energy of 600 eV. Polarization was calculated using the Berry-phase approach [48]. The presented values of the Kohn-Sham eigenvalues, the Ewald energy, and the Hartree energy were from the values reported in the VASP output. We used the ISOTROPY software suite to aid with the group-theoretic analysis [49].

B. Origin of the anti-parallel distortion of atoms at the Cu and In sites

The anti-parallel distortion between the Cu and In atoms can be understood by studying their local bonding network. Fig. 5 shows the top-view of the structural distortions within a single layer in the FiE phase relative to the PE phase. The three Cu atoms around the central In atom (in broken black circle) are labeled 1-3. Distortions into (out of) the plane are denoted by ‘×’ (broken circles). At each atomic site only the dominant symmetry adapted distortion is shown for clarity.

The presented values of the Kohn-Sham eigenvalues, the Ewald energy, and the Hartree energy were from the values reported in the VASP output. We used the ISOTROPY software suite to aid with the group-theoretic analysis [49].
C. Improved fit for the Landau free energy

The fit to the energy surface can be improved by using additional coupling terms ($c_{22}$, $c_{24}$) in the Landau free energy expansion about the PE phase. This new free energy ($F$) can be written as,

$$F = E_0 + b_{02}Q_{12}^2 + b_{04}Q_{2-}^4 + b_{06}Q_{1-}^6$$

$$+ b_{08}Q_{1-}^8 + c_{12}Q_{1+}Q_{2-}^2 + c_{22}Q_{1+}^2 + Q_{1-}^2$$

$$+ c_{14}Q_{1+}Q_{4-}^4 + c_{24}Q_{1+}^2 + Q_{1-}^4 + a_{20}Q_{1+}^2.$$  (3)

While a term that is linear in the fully symmetric mode ($Q_{1+}$) is symmetry allowed, we do not include this as the PE phase is fully relaxed. The fitted coefficients are shown in Table VI. While these additional terms improve the fit to the total energy, we note that our conclusions in the main text are qualitatively unaffected.

D. Remarks on the total energy decomposition

It is important to point out that the discussion in the main text decomposing the total energy into its contributions from the Kohn-Sham electronic energy and the Ewald energy fails to explain all the features we find in the total energy surface. This highlighting the importance of the other contributions to the total energy including the Hartree term - the electron-electron interaction energy. Fig 6 shows that Hartree term typically competes with the Ewald energy, leading to partial cancellation between the two contributions. However, the energy gain from the Hartree term on condensation of the polar mode (0.51 eV/Cu) is not enough to overcome the energy penalty from the Ewald term (14.1 eV/Cu). Other contributions to the total energy need to be taken into account to explain all the features in the total energy surface. But we note that, the presented energy-decomposition provides a simple model to understand the microscopic origin of the coupling between the polar mode and the fully symmetric mode.

E. Polarization as a function of modes

Figure 7 shows the total polarization as a function of the distortions in the FiE phase with respect to the PE phase. It is evident that the fully-symmetric mode on its own does not carry any polarization. While the condensation of the fully symmetric mode on top of the polar mode modifies the electronic polarization, the polar mode carries most of the polarization in the system. As the metal atom distortions dominate the polar mode, we can conclude that the metal atoms carry most of the polarization in FiE CIPSe.

F. Atom-projected bandstructure

Fig. 8 shows the atom-projected bandstructure of (a) the PE and (b) FiE phase along the high-symmetry directions in the two-dimensional Brillouin zone. The FiE phase has a larger band gap compared to the PE phase. Further, the structural distortions in the FiE phase rel-
ative to the PE phase leads to a change in the atom-projected contributions to the band edges. This is most evident in the valence band maximum (VBM). In the PE phase the VBM has contributions from both the Cu (red) and Se (cyan) atoms. In the FiE phase the contribution to the VBM from the Cu atom is smaller while the contribution from the Se atoms dominates the bands. This suggests a charge transfer between the Cu and Se atoms from the PE phase to the FiE phase.

G. Anharmonic stabilization in the monolayer limit

To check the validity of our mechanism of stabilization of polarization, we performed similar calculations for three different cases. We considered a monolayer including dipole correction (see Fig. 9 (a)), as well as two cases where one of the layers in the bulk unit cell is constrained to be PE (see Fig. 9 (b)), and the other is FiE (see Fig. 9 (c)). For simplicity we calculated the total energy using the same distortions for the polar mode and the fully symmetric mode as in the bulk fully-relaxed case. We observed a strong stabilization of the polar phase due to the anharmonic coupling between the polar mode and the fully symmetric mode in all the cases.
FIG. 9. The energy surface as a function of the fractional amplitude of the fully symmetric mode ($Q_{Γ_1}$) and the polar mode ($Q_{Γ_2}$). (a) Monolayer, (b) bulk with one layer fixed to PE phase, (c) bulk with one layer fixed to FiE-phase. All the reported energies are relative to the fully-relaxed PE phase ($P31c$).